

**TMS 2007 ELECTRONIC
MATERIALS
CONFERENCE**
and Exhibition

June 20-22, 2007
University of Notre Dame
Notre Dame, Indiana

Final Program

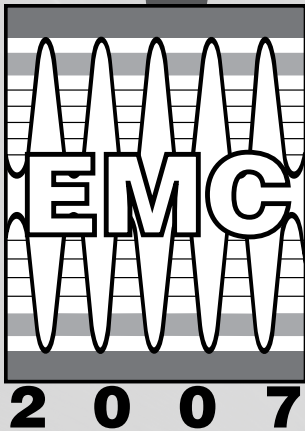
Sponsored by

TMS

Electronic, Magnetic & Photonic Materials Division

TMS 2007 Electronic Materials Conference

June 20-22, 2007 • University of Notre Dame • Notre Dame, Indiana



Welcome to the Premier Annual Forum on the Preparation and Characterization of Electronic Materials

Your registration includes:

- Technical Sessions
- Exhibition
- Welcoming Reception
- Coffee Breaks
- Thursday Banquet*

**One-day registration does not include Thursday banquet.*

Value for Your Cost

EMC is being coordinated with the Device Research Conference, also held on-site, June 18-20. Badges will be accepted for admittance to both conferences on Wednesday.

Technical Sessions

Technical sessions commence with the plenary session on Wednesday at 8:20 a.m. in the Leighton Concert Hall of the DeBartolo Performing Arts Center. The Center is located off Notre Dame Avenue near the university's main entrance at the south end of DeBartolo Quad. All subsequent technical sessions will be held in DeBartolo Hall.

Audio/Video Recording

TMS reserves the right to all audio and video reproductions of presentations at TMS sponsored meetings. Recording of sessions (audio, video, still photography, etc.) intended for personal use, distribution, publication, or copyright without the express written consent of TMS and the individual authors is strictly prohibited.

Refund

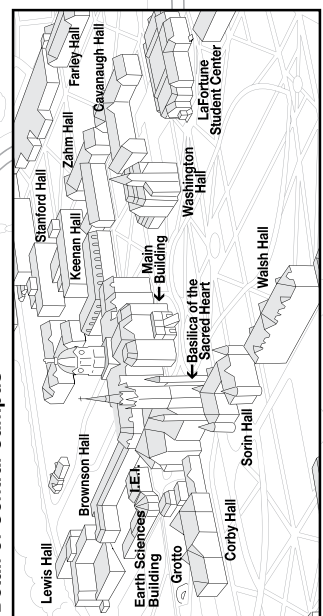
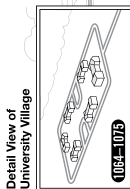
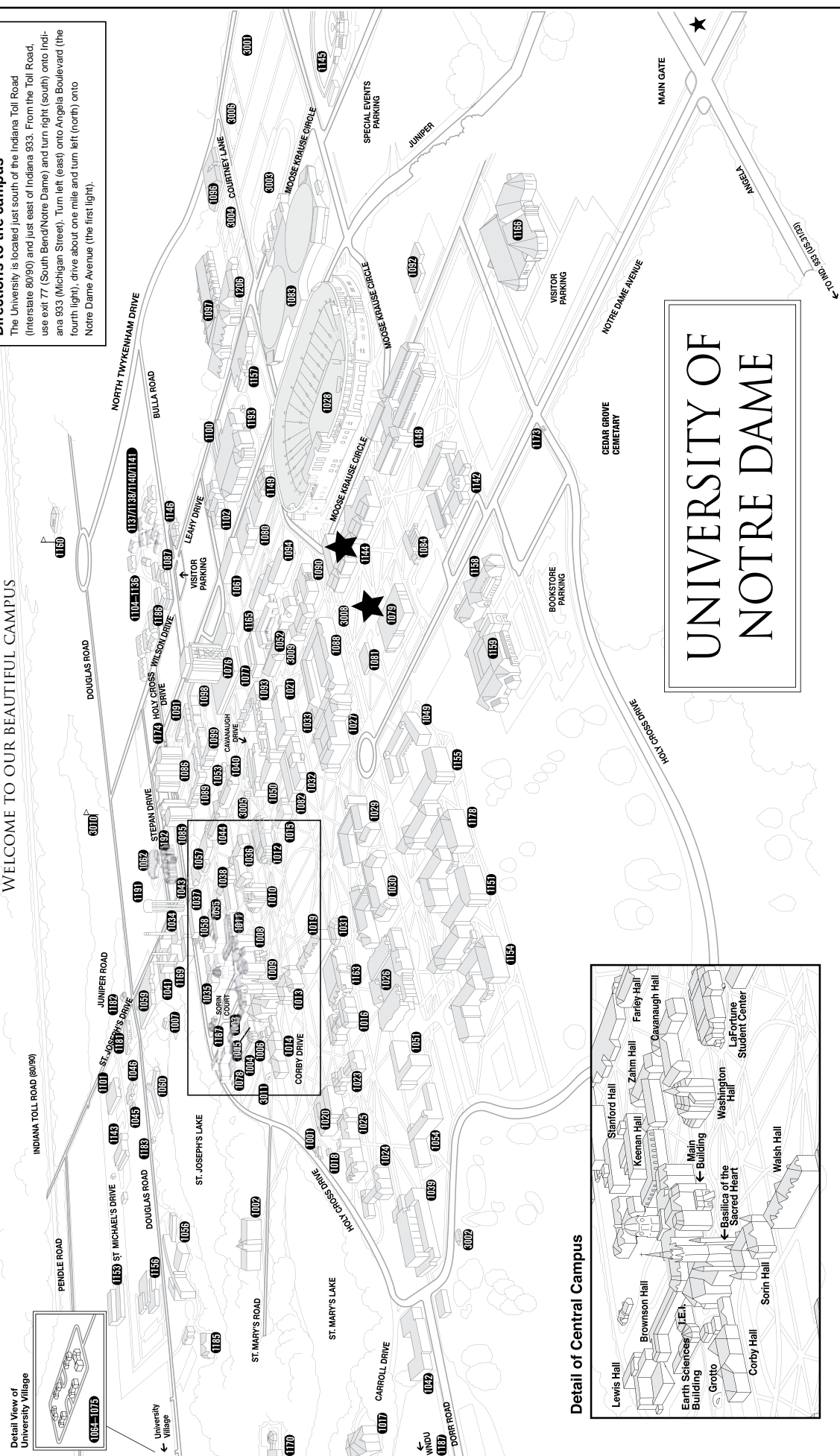
The deadline for refunds was June 4, 2007. No refunds are issued at the meeting.

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Directions to the campus
 The University is located just south of the Indiana Toll Road (Interstate 80/90) and just east of Indiana 933. From the Toll Road, use exit 77 (South Bend/Notre Dame) and turn right (south) onto Indiana 933 (Michigan Street). Turn left (east) onto Angela Boulevard (the fourth light), drive about one mile and turn left (north) onto Notre Dame Avenue (the first light).

WELCOME TO OUR BEAUTIFUL CAMPUS



UNIVERSITY OF NOTRE DAME

MAP COURTESY OF NOTRE DAME ALUMNI ASSOCIATION

ALPHABETICAL LISTING OF CAMPUS BUILDINGS

1008	Admissions (Main Building)	1005	Institute for Educational Initiatives
1009	Alumni Association	1006	Isis Gallery (Riley Hall of Art and Design)
1158	Alumni Soccer Field	1021	Ivy Softball Hall
3001	Alumni Soccer Field	1036	Joyce Center (Joyce Athletic and Convocation Center)
1029	Alumni Hall	1083	Joyce Center (Joyce Athletic and Convocation Center)
1029	Architecture	1093	Jordan Science Learning Center
1090	Art Gallery	1059	Keenan Hall
1083	Athletic and Convocation Center (Joyce Center)	1078	Keogh Hall
1156	Ave Maria Press	1085	Knights of Columbus Council Hall
1016	Badin Hall	1098	Knott Hall
1100	Band Building	1043	LaFortune Student Center
1009	Basilica of the Sacred Heart	1002	LaFortune Student Center
1007	Boat House	1163	LaFortune Student Center
1020	Bond Hall (Architecture)	1067	LaFortune Student Center
1159	Brown-Norris Dame Bookstore	1072	LaFortune Student Center
1040	Brownson Hall	1078	LaFortune Student Center
1003	Burke Memorial Golf Course	1003	LaFortune Student Center
3002	Burke Memorial Golf Course	1078	LaFortune Student Center
1012	Caletaria (LaFortune Student Center/Huddle)	1088	LaFortune Student Center
1057	Caletaria (North Dining Hall)	1085	LaFortune Student Center
1026	Caletaria (South Dining Hall/Reckers)	1153	LaFortune Student Center
1063	Campus Computer/Math	1080	LaFortune Student Center
1017	Carroll Hall	1078	LaFortune Student Center
3003	Carter Field	3002	LaFortune Student Center
1036	Cedar Grove Cemetery	1086	LaFortune Student Center
1079	Center for Continuing Education (McKenna Hall)	1206	LaFortune Student Center
1053	Center for Social Concerns	1097	LaFortune Student Center
1063	Clarke Memorial Fountain	1097	LaFortune Student Center
1163	Clark Center for Campus Ministry	1159	LaFortune Student Center
1163	Coleman-Morse Centers	1163	LaFortune Student Center
1163	Columbia Hall	1080	LaFortune Student Center
1014	Courtesy Tennis Center	1019	LaFortune Student Center
3004	Courtesy Tennis Center	1019	LaFortune Student Center
1181	(Notre Dame) Credit Union	1082	LaFortune Student Center
1015	Crowley Hall of Music	1015	LaFortune Student Center
1033	Cushing Hall of Engineering	1142	LaFortune Student Center
1166	the Performing Arts	1142	LaFortune Student Center
1144	DeBarotolo Hall	1040	LaFortune Student Center
1094	DeCro Faculty Hall	1060	LaFortune Student Center
1030	Dillon Hall	1012	LaFortune Student Center
1146	Early Childhood Development Center	1146	LaFortune Student Center
1004	Earth Sciences Building	1062	LaFortune Student Center
1174	East Gate	1091	LaFortune Student Center

ABOUT THE UNIVERSITY OF NOTRE DAME

History and Governance
The University of Notre Dame was founded in 1842 by a young priest of a French missionary order called the Congregation of Holy Cross and seven Holy Cross brothers. Father Edward F. Sorin started his school in the northern Indiana wilderness with about \$500 and three log buildings in bad repair, and in 1844 he received a charter from the state legislature. His initial educational program adapted the classic liberal arts curriculum to the needs of the frontier. Science entered the curriculum in 1865, followed by law (1869) and engineering (1873), the last two academic offerings being the first under Catholic auspices in America. A graduate program came in 1918, followed by the College of Business Administration in 1921. The University was governed by the Holy Cross Fathers until 1967, when it became

one of the first major Catholic universities to transfer governance to a lay Board of Trustees. Rev. John L. Jenkins, C.S.C., is Notre Dame's 17th president.

Physical Campus and Plant
Notre Dame's 1,250-acre campus, with its twin lakes and wooded areas, is located just north of the city limits of South Bend, Ind., and is part of a metro population area of more than 258,000. The University's physical plant has an insured replacement value of more than \$2.2 billion and includes some of the world's most recognized campus landmarks.

Academic Program
Notre Dame's main academic units are the four undergraduate colleges—Arts and Business, Science, Engineering, and Business—and the School of Architecture. On the post-baccalaureate level,

NUMERICAL LISTING OF CAMPUS BUILDINGS

1001	Pasquerilla Hall West	1089	Post Office
1002	Power Plant	1192	Power Plant
1003	Presbytery	1034	Presbytery
1004	Provinciate Archives Center	1066	Provinciate Archives Center
1005	Radiation Research Building	1077	Radiation Research Building
1006	Reckers Public Cafeteria	1026	Reckers Public Cafeteria
1007	Reckers Public Cafeteria	1045	Reckers Public Cafeteria
1008	Reyniers Life Annex	1046	Reyniers Life Annex
1009	Riley Hall of Art and Design	1021	Riley Hall of Art and Design
1010	Rocke Aquatic Center	1083	Rocke Aquatic Center
1011	Rocke Aquatic Center	1083	Rocke Aquatic Center
1012	Rocke Aquatic Center	1083	Rocke Aquatic Center
1013	Rocke Aquatic Center	1083	Rocke Aquatic Center
1014	Rocke Aquatic Center	1083	Rocke Aquatic Center
1015	Rocke Aquatic Center	1083	Rocke Aquatic Center
1016	Rocke Aquatic Center	1083	Rocke Aquatic Center
1017	Rocke Aquatic Center	1083	Rocke Aquatic Center
1018	Rocke Aquatic Center	1083	Rocke Aquatic Center
1019	Rocke Aquatic Center	1083	Rocke Aquatic Center
1020	Rocke Aquatic Center	1083	Rocke Aquatic Center
1021	Rocke Aquatic Center	1083	Rocke Aquatic Center
1022	Rocke Aquatic Center	1083	Rocke Aquatic Center
1023	Rocke Aquatic Center	1083	Rocke Aquatic Center
1024	Rocke Aquatic Center	1083	Rocke Aquatic Center
1025	Rocke Aquatic Center	1083	Rocke Aquatic Center
1026	Rocke Aquatic Center	1083	Rocke Aquatic Center
1027	Rocke Aquatic Center	1083	Rocke Aquatic Center
1028	Rocke Aquatic Center	1083	Rocke Aquatic Center
1029	Rocke Aquatic Center	1083	Rocke Aquatic Center
1030	Rocke Aquatic Center	1083	Rocke Aquatic Center
1031	Rocke Aquatic Center	1083	Rocke Aquatic Center
1032	Rocke Aquatic Center	1083	Rocke Aquatic Center
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1036	Rocke Aquatic Center	1083	Rocke Aquatic Center
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1038	Rocke Aquatic Center	1083	Rocke Aquatic Center
1039	Rocke Aquatic Center	1083	Rocke Aquatic Center
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1047	Rocke Aquatic Center	1083	Rocke Aquatic Center
1048	Rocke Aquatic Center	1083	Rocke Aquatic Center
1049	Rocke Aquatic Center	1083	Rocke Aquatic Center
1050	Rocke Aquatic Center	1083	Rocke Aquatic Center
1051	Rocke Aquatic Center	1083	Rocke Aquatic Center

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1052	O'Shaughnessy Hall	1052	O'Shaughnessy Hall
1053	Center for Social Concerns	1053	Center for Social Concerns
1054	Early Childhood Development Center	1054	Early Childhood Development Center
1055	Menzoza College of Business	1055	Menzoza College of Business
1056	Hank Family Center	1056	Hank Family Center
1057	North Dining Hall	1057	North Dining Hall
1058	Food Services Support Facility (Joyce Center)	1058	Food Services Support Facility (Joyce Center)
1059	Facilities/Maintenance Center	1059	Facilities/Maintenance Center
1060	Wash Hall	1060	Wash Hall
1061	Wash Hall	1061	Wash Hall
1062	Wash Hall	1062	Wash Hall
1063	Wash Hall	1063	Wash Hall
1064-1075	Wash Hall	1064-1075	Wash Hall
1076	Wash Hall	1076	Wash Hall
1077	Wash Hall	1077	Wash Hall
1078	Wash Hall	1078	Wash Hall
1079	Wash Hall	1079	Wash Hall
1080	Wash Hall	1080	Wash Hall
1081	Wash Hall	1081	Wash Hall
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1101	Wash Hall	1101	Wash Hall
1102	Wash Hall	1102	Wash Hall
1103	Wash Hall	1103	Wash Hall
1104-1136	Wash Hall	1104-1136	Wash Hall
1137-1138/1140/1141	Wash Hall	1137-1138/1140/1141	Wash Hall
1142	Wash Hall	1142	Wash Hall
1143	Wash Hall	1143	Wash Hall

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Alumni
The University has 118,000 plus Alumni, most of them organized into a worldwide network of 264 alumni clubs.

Finances
The current budget totals almost \$700 million, and the endowment is about \$5 billion at estimated market value. Since 1960, the University has received more than \$2.2 billion in gifts and grants.

Student Body
Notre Dame is one of a handful of truly national universities—its student body comes from all over the country. It is also a residential university, with 80 percent of its undergraduates living in 27 campus halls.

While intercollegiate sports, particularly Notre Dame's legendary football team, are an important facet of student life, the University's varsity athletes meet the same academic standards required of all students and graduate at about the same rate: 90 percent or better.

Among the top 20 major universities, Notre Dame has the highest percentage of students studying abroad.

Tuition and Student Aid
Undergraduate tuition for the 2006-2007 academic year is \$33,407 with room and board averaging \$8,730. More than three-fourths of Notre Dame undergraduates receive some sort of financial aid which in 2005-2006 totalled more than \$1.55 million from all sources. Graduates received approximately \$87.5 million.

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Computer/Network Facilities

Registrants have guest access to selected computer workstations, wireless and Ethernet Internet connection points within Notre Dame's information technology infrastructure. Access information with a temporary username and password are provided upon check-in. Notre Dame's NOMAD wireless network provides Internet access in all residence hall rooms, DeBartolo Hall classrooms, McKenna Hall and several public areas. Each technical session room has a video projector, a VGA connection for a laptop, and a Windows workstation equipped with Microsoft PowerPoint and Adobe Acrobat software.

Messages

A message board is located near the EMC registration desk in McKenna Hall. Messages will be posted on the board throughout the conference.

South Dining Hall Hours

Breakfast	7 to 8 a.m.
Lunch	11:45 a.m. to 1:15 p.m.
Dinner	5:30 to 7 p.m.

Food facilities on campus close at 7 p.m.; no refunds are made for late arrivals, early departures or missed meals.

Commuter Lunch

Individuals with off-campus housing may buy meals individually at the university's dining hall. Cash only, please.

Parking

Please pay particular attention to any construction on campus. Be prepared for detours and follow instruction signs and security officials.

Visitor Parking

- Parking is restricted to the conference/visitors lot west of the DeBartolo Center for the Performing Arts at the entrance to campus.
- Coupons to exit the lot (\$1 each) are available for purchase at the information desk of the Center for Continuing Education (CCE) in McKenna Hall. (price at gate, \$2 each)
- Parking fee is not included in the cost of housing.
- Parking for handicapped guests with appropriate license designations or stickers is available directly adjacent to CCE.
- Cars parked in areas not designated for visitors will be ticketed and towed.

Campus Smoking Policy

The university prohibits smoking in all buildings, including residence halls. Smoking is permitted in designated areas outside.



Americans With Disabilities Act

TMS strongly supports the federal Americans with Disabilities Act (ADA) which prohibits discrimination against, and promotes public accessibility for, those with disabilities. In support of, and in compliance with, ADA, we ask those requiring specific equipment or services to indicate their needs at the EMC registration desk.

Networking and Social Events

Welcoming Reception for Attendees

Wednesday, 6 to 8 p.m.

McKenna Hall

Great Hall of the Century

Thursday, 6 to 9 p.m.

Downtown South Bend, Indiana

Spend the evening enjoying the unique Century Center, situated on an 11-acre park on the St. Joseph River in downtown South Bend. A catered dinner will be served to live musical entertainment in the Great Hall, where a three-story window overlooks cascading whitewater rapids. After dinner, participants may visit the attached College Football Hall of Fame, one of the world's major sports shrines, and the South Bend Regional Museum of Art.

Tickets:

- Cost includes dinner, admission to the museum and the Hall of Fame, and bus transportation between the University of Notre Dame and Century Center.
- Free to full conference and student registrants
- \$60 for adults (guests and one-day registrants) and \$25 for children 12 and under
- Purchase tickets at the EMC registration desk until 5 p.m. on Wednesday.

Informal Coffee Breaks for Attendees

Take a break throughout the day and enjoy coffee, tea or sodas.

Exhibition Area, McKenna Hall

Recreation

Notre Dame's recreational facilities are available to conference guests. Name tags must be worn at all times and room keys must be presented in order to use the recreational facilities:

- Golf
- Swimming
- Racquetball
- Basketball
- Squash
- Weightlifting
- Tennis

Schedules and reservation information are included in your conference packet. Walking and jogging route maps marked with distances are available at the information desk in the Center for Continuing Education, McKenna Hall. For further facility information, visit www.nd.edu/~recsport.

Visit McKenna Hall and find equipment, instrumentation, software, publications and services in these areas:

- Advanced thin-film characterization
- Chemical Vapor Deposition (CVD)
- Compound semiconductor materials
- Failure analysis
- GaAs and InP-based epitaxial wafers, substrates
- High performance purification
- High purity metalorganics
- III-V materials
- Materials characterization
- MOCVD
- Optoelectronics
- Sapphire substrates
- Scanning probe and electron microscopes
- Silicon heterostructures
- Ultra High Purity (UHP) metals, gas and chemical
- Wafer processing equipment
- Wide bandgap semiconductors

Exhibit Dates and Hours

Wednesday 9:30 a.m. to 4 p.m.
6 to 8 p.m. (in conjunction with Welcoming Reception)

Thursday 10 a.m. to 4 p.m.

Exhibiting Companies (as of May 23)

Akzo Nobel

Andeen-Hagerling Inc.

Cree Inc.

Epichem Group

Evans Analytical Group

Horiba Jobin Yvon Inc.

k-Space Associates Inc.

Lake Shore Cryotronics Inc.

Lehightronics Inc.

MMR Technologies Inc.

Omicron NanoTechnology USA

Park Systems

Riber

SVT Associates Inc.

United Mineral & Chemical Corporation

Vacuum Barrier Corporation

Veeco Instruments Inc.

Wafer Technology Ltd.

WEP-DAGE

EMC thanks the following corporate sponsors:

k-Space Associates Inc. for providing lanyards

United Mineral & Chemical Corporation for providing Wednesday morning's coffee break

Awards

John Bardeen Award

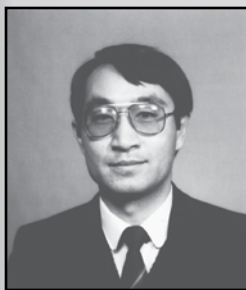
Established in 1994, this award recognizes an individual who has made outstanding contributions, and is a leader, in the electronic materials field.

2007 Recipient: Sungho Jin

Citation: For seminal contributions to the science and technology of electronic materials, from the invention of hard magnetic materials to the practical processing of high-temperature superconductors to the discovery of colossal magnetoresistance.

Sungho Jin is a professor at the University of California, San Diego. Prior to joining the university in 2002, where he currently serves as director of the materials science and engineering program, Dr. Jin performed research for Bell Labs for 26 years. He earned his doctorate in materials science and engineering from the University of California, Berkley.

Dr. Jin has contributed to the advancement of science and technology with world-class, trend-setting research in the fields of electronic, magnetic, optical, superconducting, electronic packaging and bio materials. He has published more than 260 papers and is a member of the U.S. National Academy of Engineering, a Fellow of the American Physical Society, a TMS Fellow, and a Fellow of the American Society for Metals as well as the recipient of the 2005 Nano 50 Award.



"It is a great honor to be selected as the recipient of the 2007 John Bardeen Award. This recognition means a lot to me. After spending almost three decades of my life working on electronic, magnetic and superconducting materials, receiving this prestigious award, named after the great scientist John Bardeen, is very rewarding and makes me happy." – Sungho Jin

Nominate Your Colleague for the TMS 2009 John Bardeen Award!

About John Bardeen

John Bardeen's career of theoretical and experimental research set the foundation for the current state of understanding of electronic materials. Two areas in which Bardeen had great impact were the invention and development of the solid-state transistor and the theory that developed greater understanding of superconductivity.

For Award Criteria and Additional Information

Pick up a nomination form at the EMC registration desk, or visit the TMS Web site at www.tms.org/Society/honors.html.

2006 Student Paper Awards

Wednesday (Plenary Session)

Leighton Concert Hall

Awards of \$500 each are given to the authors of the top 5-percent of student papers presented at EMC. Student papers are judged on both scientific content and oral presentation. Awards are funded by the Electronic Materials Committee and presented at the following year's EMC conference.

Student: Xiaodong Chen, *Cornell University*

Paper: Direct Write Composition Patterning of InGaN during Molecular Beam Epitaxy

Advisor: Dr. William J. Schaff

Student: Shadi Dayeh, *University of California, San Diego*

Paper: Growth Mechanism and Optimization of InAs Nanowires Synthesized by OMVPE

Advisor: Professor Deli Wang and Professor Edward T. Yu

Student: Nathan Yoder, *Northwestern University*

Paper: Investigating the Stability of Organic Molecules Bound to Semiconductor Surfaces with Low Temperature UHV-STM

Advisor: Professor Mark Hersam

Attention Students!

**Become a member of the Material Advantage student program
for only \$25 and reap the benefits of four varied
materials organizations!**

ACerS = The American Ceramic Society

AIST = Association for Iron & Steel Technology

ASM = ASM International

TMS = The Minerals, Metals & Materials Society

For full details on benefits, including scholarships and awards totaling more than \$600,000, **visit www.materialadvantage.org.**

Material Advantage

Everything Else Is Immaterial!

EMC does not publish formal conference proceedings; however, conference abstracts are published in the *Journal of Electronic Materials* (*JEM*) throughout the year. *JEM* encourages both presenters and attendees to submit manuscripts of their work.

About *JEM*

JEM is a monthly archival technical journal of TMS and the Institute of Electrical and Electronics Engineers (IEEE). Articles are reviewed, selected and edited by peers who serve as voluntary members of the editorial board, the board of associate editors, or section editors.

JEM's Content

JEM is a forum for the rapid circulation of the results of original research. It contains technical papers detailing critical new developments in the electronic materials field, as well as invited and contributed review papers on topics of current interest. The journal welcomes articles on the preparation of electronic materials and the evaluation of their chemical, physical and electronic properties. Specific areas of interest include electronic device structures, electronic packaging, detectors, emitters, metallization, superconductors, recording media, superlattices, and nanoscale materials and devices.

JEM Subscription

2008 *JEM* issues will include manuscripts of papers presented at the 2007 EMC with a special issue on group III nitrides, SiC and ZnO. Individuals may subscribe to *JEM* by contacting Springer, the journal's publisher, at:

In North America

Telephone (800) 777-4643 / E-mail journals-ny@springer.com

Outside North America

Telephone (212) 460-1500 or +49 (0) 6221-345-4303 / E-mail subscriptions@springer.com

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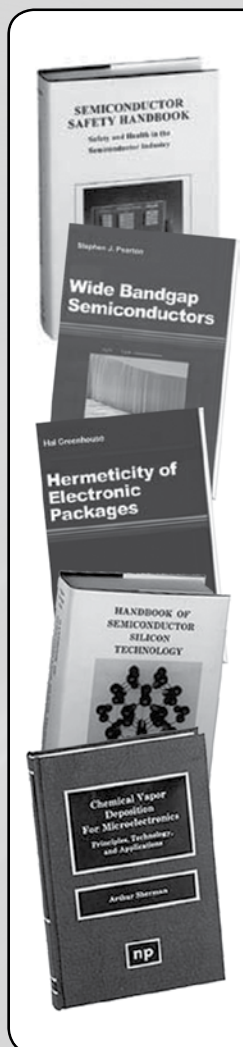
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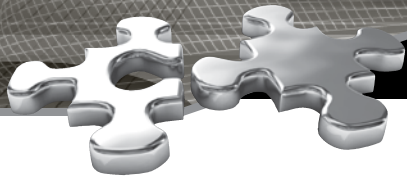
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Wednesday AM, June 20, 2007					
8:20 AM		EMC PLENARY LECTURE/STUDENT AWARDS			
Room:		DeBartolo Performing Arts Center, Leighton Concert Hall			
Plenary Speaker:		Alan J. Heeger, University of California, Santa Barbara			
Topic:		"Low Cost 'Plastic' Solar Cells: A Dream or Reality???"			
Break:		9:20 AM–10:00 AM			
Session A: Chemical and Biological Sensors I Room: 126		Session B: Organic/Inorganic Hybrid Photovoltaic Room: 129		Session C: III-Nitride Electronic Devices Room: 102	
10:00 AM	A1, Gateless GaN/AlGaIn BioFETs for Direct Biomolecular DetectionKendra McCoy	10:00 AM	B1, (Student), Surface Plasmon Polariton Mediated Energy Transfer in Organic Photovoltaic DevicesTimothy Heidel	10:00 AM	C1, (Student), High-Mobility Ultrashallow Pseudomorphic AlN/GaN Heterojunctions by MBEYu Cao
10:20 AM	A2, Surface Functionalization of AlGaIn for Biosensor ApplicationsXuejin Wen	10:20 AM	B2, Fiber Based Organic Light Emitting Diodes and Photovoltaic CellsBrendan O'Connor	10:20 AM	C2, (Student), Properties of GaN Buffer Layers on 6H-SiC Grown by Ammonia Molecular Beam Epitaxy for High Electron Mobility TransistorsAndrea Corrion
10:40 AM	A3, (Student), Thermodynamic Analysis of Hydrogen Sensing in Pt/AlGaIn/GaN Schottky DiodesJunghui Song	10:40 AM	B3, (Student), Subwavelength Metal Gratings as Flexible and Transparent Electrodes in Organic Thin-Film Photovoltaic CellsJung-Yong Lee	10:40 AM	C3, Extraction of Transport Dynamics in AlGaIn/GaN HFETs through Free Carrier AbsorptionYuh-Renn Wu
11:00 AM	A4, Performance Enhancement and Sensing Mechanism of Pd/AlGaIn/GaN Hydrogen Sensors Subjected to Oxygen GetteringHideki Hasegawa	11:00 AM	B4, Flexible Conjugated Polymer Photovoltaic Cells with Controlled Nanoscale Heterojunctions Fabricated Using Nanoimprint LithographyMyung-Su Kim	11:00 AM	C4, Scanning Ion Probe Studies of Silicon Implantation Profiles in AlGaIn/GaN HEMT HeterostructuresGiacinta Parish
11:20 AM	A5, (Student), Effect of Alkaline Treatment on the Characteristics of AlInN/GaN Heterostructures in ElectrolytesCarsten Pietzka	11:20 AM	B5, Electric-Field-Assisted Aerosol Deposition of Metal Nanoparticles for Surface-Plasmon-Enhanced Organic Photovoltaic CellsShigeo Fujimori	11:20 AM	C5, (Student), A Study of Post-Bombardment Effects of Electronegative Ions on the Two-Dimensional Electron Gas Properties of AlGaIn/GaN HeterostructuresAnirban Basu
11:40 AM	A6, (Student), ZnO Film/ZnO Nanowire Arrays/ZnO Film Hybrid Nanostructures for Sensor ApplicationsMin-Chang Jeong	11:40 AM	B6, (Student), Matrix-Assisted Pulsed Laser Evaporation of Hybrid Colloidal Quantum Dot/Conducting Polymer Nanocomposite HeterostructuresRyan Pate	11:40 AM	C6, Crystalline SiN _x Ultrathin Films Grown on AlGaIn/GaN by In-Situ Metalorganic Chemical Vapor DepositionToshiyuki Takizawa

Wednesday AM-PM, June 20, 2007

Session D: Spin in Low Dimensional Systems Room: 155		Session E: Non-Destructive Testing Room: 131		Session F: Germanium and Silicon Nanowires Room: 126	
10:00 AM	D1, (Student), Transport in Room-Temperature Ferromagnetic (Ga,Mn)N NanowiresMoon-Ho Ham	10:00 AM	E1, GaSb(001) Surface Reconstructions Measured at the Growth Front by Surface X-Ray DiffractionBrad Tinkham	1:30 PM	F1, Germanium Nanowires: Growth and ApplicationsEric Garfunkel
10:20 AM	D2, (Student), Calculation of Lande g-Factors and Comparison with Experiment for III-V Nanowhisker Quantum DotsAmrit De	10:20 AM	E2, X-Ray Reflectivity Based Metrologies for the Development of Metamorphic Semiconductor Device StructuresBenjamin Poust	1:50 PM	F2, (Student), Experimental and Theoretical Transport Characterization of Germanium NanowiresPaul Leu
10:40 AM	D3, (Student), Exchange Coupling in Quantum Wire Quantum DotsLingxiao Zhang	10:40 AM	E3, (Student), Temperature Dependent Stress Distribution in Heterogeneous Wafer Bonded Structures by Double Crystal X-Ray Diffraction ImagingMichael Jackson	2:10 PM	F3, (Student), Manganese-Mediated Growth of Ge/Mn _x Ge _{1-x} Nanowire HeterostructuresJessica Lensch
11:00 AM	D4, Transport Spectroscopy in a Few-Electron Quantum DotsDmitriy Melnikov	11:00 AM	E4, (Student), Indium Adlayer Kinetics on Gallium Nitride (0001) Surfaces: Monitoring Indium Segregation and PrecursorSoojeong Choi	2:30 PM	F4, (Student), Synthesis of Epitaxially-Aligned Ge/Si Core-Shell NanowiresIrene Goldthorpe
11:20 AM	D5, (Student), Enhanced Spin-Orbit Interaction in Strained InGaAs/AlGaAs Heterostructure for Spin TransistorsTakashi Matsuda	11:20 AM	E5, (Student), Fast Corona-Voltage Metrology Characterization of 3C-SiC Oxide StructuresEugene Short	2:50 PM	F5, (Student), Size Effects in the Vapor-Liquid-Solid Growth of Si, Si _{1-x} Ge _x and Si/Si _{1-x} Ge _x Heterostructure NanowiresPramod Nimmatoori
11:40 AM	D6, Late News	11:40 AM	E6, Photoluminescence Study of Self-Assembly of Heterojunction Quantum Dots(HeQuaDs)Kurt Eyink	3:10 PM	Break
				3:30 PM	F6, (Student), Nano-Imprint Lithography for Nanowire FabricationFahmida Ferdousi
				3:50 PM	F7, Late News
				4:10 PM	F8, (Student), Does the Catalyst Influence Minority Carrier Diffusion in VLS-Grown Silicon Nanowires?Jonathan Allen
				4:30 PM	F9, (Student), Using Real Time Microscopy to Quantitatively Determine Nucleation Mechanisms and Kinetics during the Growth of Si Nanowires on Si ₃ N ₄ SubstratesBong Joong Kim
				4:50 PM	F10, Late News

Wednesday PM, June 20, 2007

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1:30 PM	G1, Microstructure-Performance Correlation for Solution Processed Small Molecule TFTsDavid Gundlach	1:30 PM	H1, (Student), Nitride Nanorod Arrays for Phosphor-Free White Light Emitting DiodesParijat Deb	1:30 PM	I1, (Student), Selective GaAs Quantum Dot Array Growth Using Diblock Copolymer NanopatterningJoo Hyung Park
1:50 PM	G2, (Student), Ordered and Microstructured Thin Films in Spin Cast F-TES-ADT OTFTsSungkyu Park	1:50 PM	H2, High Brightness and High External Efficiency InGaN/GaN Light Emitting Diodes on Semipolar {10-1-1} Bulk GaN SubstratesAnurag Tyagi	1:50 PM	I2, Controlled Nucleation of InAs Quantum Dots Using Focused Ion BeamsHugh McKay
2:10 PM	G3, (Student), Charge Transport Measurements on Anisotropic Polythiophene Thin Films Fabricated via Directional CrystallizationLeslie Jimison	2:10 PM	H3, Characterization of Green LED Using p-InGaN and p-InGaN/p-GaN Superlattices as p-Type LayerJianping Liu	2:10 PM	I3, (Student), Controlled Growth of Quantum Dots and Nanopillars on Patterned GaAs Substrate by MOCVDPing-Show Wong
2:30 PM	G4, Nanoscale Measurements of Density of States and Einstein Relation in Molecular Thin Film TransistorsYossi Rosenwaks	2:30 PM	H4, Junction Temperature Analysis of GaInN/GaN Multi-Quantum Well Light Emitting Diodes by Micro-Raman SpectroscopyJayantha Senawiratne	2:30 PM	I4, Formation and Coarsening of Ga Droplets on Focused-Ion Beam Irradiated GaAs SurfacesBen Cardozo
2:50 PM	G5, Late News	2:50 PM	H5, (Student), Growth and Characterization of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ Ultraviolet Avalanche Photodiodes on GaN SubstratesDongwon Yoo	2:50 PM	I5, (Student), Suppression of Phase Transformation in Organic Encapsulated Germanium NanoparticlesSuk Jun Kim
3:10 PM	Break	3:10 PM	Break	3:10 PM	Break
3:30 PM	G6, Frequency Response and Transient Phenomena of Pentacene Thin Film TransistorsTetsuhiko Miyadera	3:30 PM	H6, (Student), Recombination Dynamics in Ultraviolet Light-Emitting Diodes with Si-Doped $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{Al}_y\text{Ga}_{1-y}\text{N}$ Multiple Quantum Well Active RegionsKaixuan Chen	3:30 PM	I6, Growth and Characterization of GaAs Quantum Dots in $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ Grown by Molecular-Beam EpitaxyBingyang Zhang
3:50 PM	G7, (Student), Surface Electronic Properties of GaN for Use as a Hole-Injection Contact for PentaceneJohn Uhlrich	3:50 PM	H7, Radiative and Non-Radiative Lifetime Studies of Enhanced UV Emission Mechanisms in AlGaIn Containing Nanoscale Compositional InhomogeneitiesGregory Garrett	3:50 PM	I7, (Student), Fabrication and Optical Characteristics of Type-II Self-Assembled GaSb Quantum Dots Embedded in InGaAs Quantum WellArezou Khoshakhlagh
4:10 PM	G8, Suppression of Short-Channel Effect in Top-Contact Pentacene Thin Film TransistorKazuhiro Tsukagoshi	4:10 PM	H8, (Student), Spectroscopic Cathodoluminescence of V-Defects in GaInN/GaN Quantum WellsYong Xia	4:10 PM	I8, (Student), AlGaAs Microdisk Cavities with InAs Quantum Dots on Si and GaN: Fabrication and Near-Field Scanning Photoluminescence CharacterizationYaya Chu
4:30 PM	G9, (Student), Macroscopic vs. Microscopic Profile Optimization for Printed OLED Devices by Large-Area Wet Micro-PrintingHongzheng Jin	4:30 PM	H9, (Student), Characterization of Homoepitaxial and Heteroepitaxial GaInN/GaN Light Emitting Diodes by Transmission Electron MicroscopyMingwei Zhu	4:30 PM	I9, Infrared Plasmon Resonance in Semimetallic Rare Earth-V/III-V Semiconductor Composite MaterialsMichael Scarpulla
4:50 PM	G10, Electrical Characterization, Standards, and Materials Considerations for Printed Electronics ManufacturingPaul Brazis	4:50 PM	H10, Late News	4:50 PM	I10, White Light Emitting Solid State Hybrid Device of (CdSe)ZnS Quantum Dot-Near UV GaN LEDSeonghoon Lee

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1:30 PM	J1, (Invited), Fabrication and Testing of Skutterudite-Based, Thermoelectric Devices for Power Generation ApplicationsJeff Sakamoto	1:30 PM	K1, (Invited), Some Critical Materials and Processing Issues in SiC Power DevicesAnant Agarwal	
2:10 PM	J2, (Student), Fabrication of Dense, Vertical Bi ₂ Te ₃ Nanowire Array Composites for Thermoelectric Power Generators and MicrocoolersKalapi Biswas	2:10 PM	K2, Effects of Threading Screw, Threading Edge, and Basal-Plane Dislocations on the Electrical Properties of 4H-SiC Schottky DiodesBrian Skromme	
2:30 PM	J3, (Student), TiN/GaN and ZrN/ScN Metal/Semiconductor Rocksalt Nitride Superlattices for Thermionic Energy ConversionVijay Rawat	2:30 PM	K3, (Student), Evidence of Negative Bias Temperature Instability in 4H-SiC Metal Oxide Semiconductor CapacitorsMatthew Marinella	
2:50 PM	J4, (Student), Non-Equilibrium Thermoelectric Transport in Thin Film HeterostructuresMona Zebarjadi	2:50 PM	K4, The Effects of Implant Activation Anneal on the Effective Inversion Layer Mobility of SiC MOSFETsSarah Haney	
3:10 PM	Break	3:10 PM	Break	
3:30 PM	J5, (Student), Semimetallic Nanoparticles Epitaxially Embedded within III-V Semiconductors for Efficient Thermoelectric Power GenerationJoshua Zide	3:30 PM	K5, 1200 V 4H-SiC Bipolar Junction Transistors with a Record b of 70Charlotte Jonas	
3:50 PM	J6, Micro Devices for Thermoelectric Figure-of-Merit Measurements of Thin FilmsZhixi Bian	3:50 PM	K6, (Student), Terahertz Emitting Devices Based on Hexagonal Silicon CarbideGuangchi Xuan	
4:10 PM	J7, (Student), High-Temperature ZT of InGaAlAs Thin Films with Embedded ErAs NanoparticlesRajeev Singh	4:10 PM	K7, (Student), Nitrogen Doping for Low-Temperature Halo-Carbon Homoepitaxial Growth of 4H-SiCKritsa Chindanon	
4:30 PM	J8, Thin-Film Power Generator Modules of (InGaAs) _{1-x} (InAlAs) _x Embedded with ErAs NanoparticlesGehong Zeng	4:30 PM	K8, Impact of Thickness and Nitrogen Doping on Carrier Lifetime in 4H-SiC EpilayersKok-Keong Lew	
4:50 PM	J9, Late News	4:50 PM	K9, Real-Time, In-Situ Tracking of Gas Phase Carbon-to-Silicon Ratio during Hot-Wall CVD Growth of SiCBrenda VanMil	

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8:40 AM	L2, (Student), Selective Debonding of InN from Sapphire to Form Electronically Active StructuresDong Hao	8:40 AM	M2, (Student), Capacitance-Voltage Characterization on GaAs p- and n-MOS Devices with ALD HfO ₂ /Al ₂ O ₃ Laminates as Gate DielectricsTian Yang	8:40 AM	N2, First-Principles Studies of Metal (111)/ZnO{0001} InterfacesYufeng Dong
9:00 AM	L3, Low Temperature Wafer Bonding for III-V Si Photonic Integrated CircuitsDi Liang	9:00 AM	M3, (Student), Observation of Near Interface Trapping Centers in Stressed Metal Gate Hafnium Oxide Field Effect Transistors Using Spin Dependent RecombinationPatrick Lenahan	9:00 AM	N3, (Student), Improvement of the Light Output of GaN-Based LEDs by Introducing ZnO NanostructureJoon-Ho Oh
9:20 AM	L4, (Student), From (001) Silicon Direct Wafer Bonding to the Surface Nano-Patterning for the Self-Assembled Growth of NanostructuresAlexis Bavard	9:20 AM	M4, (Student), Fluorine Incorporation at HfO ₂ /SiO ₂ Interfaces in High-k Metal-Oxide-Semiconductor Gate StacksJeong-Hee Ha	9:20 AM	N4, (Student), Non-Alloyed Ohmic Contact Using Selective-Area Growth by Plasma-Assisted Molecular Beam EpitaxyHuichan Seo
9:40 AM	L5, UHV-Bonding of Si/GaAs p-n Heterojunction Using Hydrogen Ion Beam Surfaces CleaningN. Razek	9:40 AM	M5, Studies on Oxygen Conduction in Rare-Earth Doped Hafnia and Relationship to Electrical Transport PropertiesShriram Ramanathan	9:40 AM	N5, (Student), V- and Ti-Based Ohmic Contacts to Plasma-Etched n-Al _{0.58} Ga _{0.42} NMary Miller
10:00 AM	Break	10:00 AM	Break	10:00 AM	Break
10:20 AM	L6, (Student), Back-Channel Passivated Amorphous Silicon TFTs Fabricated at 300°C on a Clear Plastic SubstrateKunigunde Cherenack	10:20 AM	M6, (Student), Atomic Layer Deposition of HfO ₂ on IIIIV Semiconductors: Effects of Surface Treatment and Post-Deposition AnnealsEunji Kim	10:20 AM	N6, (Student), Ohmic Behavior and Interfacial Reaction of Si/Ti/Al/Mo/Au Ohmic Contacts on AlGaIn/GaN High Electron Mobility TransistorsLiang Wang
10:40 AM	L7, Flexible Polymeric and a-Si:H-Based Image Sensors Fabricated by Digital LithographyWilliam Wong	10:40 AM	M7, (Student), Electrical Properties of Thermally Grown TiO ₂ /SiO ₂ Stack MIM CapacitorsBing Miao	10:40 AM	N7, (Student), Effects of Mo:Al Ratios on Mo/Al/Mo/Au Ohmic Contacts for GaN-Based HEMTsAnirban Basu
11:00 AM	L8, (Student), Amorphous Silicon Thin-Film Transistor Backplanes Deposited at High Temperature on Clear Plastic for Electrophoretic DisplaysAlex Kattamis	11:00 AM	M8, (Student), Electron Spin Resonance Studies of Silicon Nano-Crystal Flash Memory DevicesJason Ryan	11:00 AM	N8, AlGaIn/GaN FETs with Un-Optimized Source/Drain Contacts for Rapid Extraction of Channel Mobility and Charge ConcentrationMichael Awaah
11:20 AM	L9, (Student), Indium Gallium Zinc Oxide as a Channel Material for Transparent Thin Film TransistorsArun Suresh	11:20 AM	M9, Depth-Resolved Cathodoluminescence Spectroscopy Study of Defects in SrTiO ₃Jun Zhang	11:20 AM	N9, (Student), Electrical Contacts to Undoped and Sulfur-Doped Nanocrystalline Diamond FilmsPranita Kulkarni
11:40 AM	L10, Late News	11:40 AM	M10, Improved Cell Performance of NO-Based Storage Dielectric by N ₂ O Treated Nitride Film for Trench DRAMChih-Ming Chang	11:40 AM	N10, (Student), Investigations of UV-Transparent Nanocrystalline Diamond Films as a Type-II Heterojunction to 4H-SiCMarko Tadjer

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8:40 AM	O2, Conduction Band and Electronic Properties of AlP-GaP SuperlatticesW. Masselink	8:40 AM	P2, Resistivity Response of Hemin Functionalized InAs to Low ppm Levels of Nitric Oxide GasMichael Garcia	8:40 AM	Q2, Spectral Characteristics of Individual Si- and C-core Partial Dislocations Obtained by Optical Emission MicroscopyKendrick Liu
9:00 AM	O3, Anisotropic Tunneling-Mediated Transport in Two-Dimensional Arrays of InAs NanostructuresW. Masselink	9:00 AM	P3, Photoelectric Junctions between GaAs and Photosynthetic Reaction Center ProteinYossi Rosenwaks	9:00 AM	Q3, (Student), Influence of Threading Dislocations on the Recombination Enhanced Partial Dislocation Glide in 4H-Silicon Carbide Epitaxial LayersYi Chen
9:20 AM	O4, (Student), Infrared Reflectivity Spectroscopy of Optical Phonons in Short-Period AlGaIn SuperlatticesJoseph Herzog	9:20 AM	P4, Characteristics of Carbon Nanotube Field-Effect Transistor Biosensor without Top-Gate Metal ElectrodeMasuhiro Abe	9:20 AM	Q4, Ti-Related Photoluminescence in 4H-SiCSerguei Maximenko
9:40 AM	O5, (Student), Transport Properties and Applications of Quantum-Wire SolidsAmol Singh	9:40 AM	P5, (Student), Fabrication and Electrical Properties of Nanoplate Field Effect Devices for Chemical and Biological Molecule SensingOguz Elibol	9:40 AM	Q5, (Student), Determination of Dislocation Sense of Micropipe via Grazing-Incidence X-Ray Topography in 4H Silicon CarbideYi Chen
10:00 AM	Break	10:00 AM	Break	10:00 AM	Break
10:20 AM	O6, (Student), Nanometer-Scale Measurements of Confined States in and between InAs/GaAs Quantum DotsVaishno Dasika	10:20 AM	P6, (Student), Fabrication and Characterization of Novel Three Terminal Nanochannel Devices for the Detection of Short BiomoleculesMurali Venkatesan	10:20 AM	Q6, (Student), Step-Induced Stacking Faults in 3C-SiC Heterofilms: Further Motive for Reducing Screw Dislocation Density in 4H-SiC SubstratesKevin Speer
10:40 AM	O7, (Student), Composition Analysis of Silicon and Germanium Nanowires Using Pulsed-Laser Atom Probe TomographyDaniel Perea	10:40 AM	P7, (Student), Biochemical Functionalization of Semiconductor Devices: Cation Selectivity and Surface ChargesSamir Iqbal	10:40 AM	Q7, (Student), 3C-SiC Growth on Different Silicon OrientationsChristopher Frewin
11:00 AM	O8, Nanoscale Strain and Composition Mapping in Quantum Dots Using Kelvin Probe Force MicroscopyYossi Rosenwaks	11:00 AM	P8, (Student), Hydrogen Interaction with Liquid Ga Nanoparticles Monitored by the Plasmon ResonancePae Wu	11:00 AM	Q8, (Student), Reduced Temperature 3C-SiC on Si Epitaxial Growth via HCl AdditiveMeralys Reyes
11:20 AM	O9, Detection of Microwave Magnetic Fields on Yttrium Iron Garnet Materials Using Heterodyne Demodulation on a Loop Probe CantileverCharles Paulson	11:20 AM	P9, (Student), Nanoparticle Light-Emitting Sol-Gel-Based Waveguide Formation and CharacterizationJinlong Zhang	11:20 AM	Q9, Late News
11:40 AM	O10, Late News	11:40 AM	P10, (Student), In Vitro Microfabrication Assembly of Mitotic-Spindle-Like StructuresYing-Ming Huang	11:40 AM	Q10, Late News

Thursday AM-PM, June 21, 2007

Session R: ZnO Growth: Films and Nanostructures Room: 141		Session S: Metamorphic Materials: Characterization and Devices Room: 126		Session T: Semiconductor Processing: Oxidation, Passivation Room: 129	
8:20 AM	R1, (Student), Growth of Polarity Controlled ZnO Films on (0001) Al ₂ O ₃Jinsub Park	1:30 PM	S1, (Student), Formation of Interfacial Misfit Array for AlSb on Miscut Si SubstrateShenghong Huang	1:30 PM	T1, Late News
8:40 AM	R2, (Student), Lattice Strain Evolution in ZnO Films Grown on MgO/c-SapphireSeunghwan Park	1:50 PM	S2, (Student), Preparation and Characterization of Relaxed Si _{0.08} Ge _{0.92} Surfaces for MBE Growth on Virtual SiGe SubstratesKatherine Dykes	1:50 PM	T2, Pulse Thermal Processing of NanomaterialsRon Ott
9:00 AM	R3, Electrical and Optical Properties of MgZnO Films Prepared by Pulsed Laser DepositionA. Y. Polyakov	2:10 PM	S3, (Student), Strain Induced Surface Reconstruction on Sb/GaAs(001)Jessica Bickel	2:10 PM	T3, (Student), Low-Temperature PECVD OLED EncapsulationDalong Zhao
9:20 AM	R4, (Student), Optical and Structural Characterization of ZnO/Mg _x Zn _{1-x} O Quantum Wells Synthesized by Pulsed Laser Deposition (PLD)Willie Bowen	2:30 PM	S4, Interfacial Structure of Tilted InAs Islands on GaAsXueyan Song	2:30 PM	T4, (Student), Passivation of Surface States for Intersubband Quantum Box (IQB) Laser StructuresManish Rathi
9:40 AM	R5, Effect of Buffer Layers on Mg _x Zn _{1-x} O Films Grown on c-Sapphire by P-MBE - A Comparison StudyZahra Vashaei	2:50 PM	S5, (Student), Lattice-Engineering for Monolithic Visible Yellow-Green Light EmittersMichael Mori	2:50 PM	T5, Fabrication of Nanometer-Scale Single Photon Detectors in InGaAsP/InP HeterostructuresMinjun Yan
10:00 AM	Break	3:10 PM	Break	3:10 PM	Break
10:20 AM	R6, Late News	3:30 PM	S6, (Student), Enhancement-Mode Metamorphic InAlAs/InGaAs HEMTs on GaAs Substrates by MOCVD and Plasma TreatmentChak Wah Tang	3:30 PM	T6, (Student), Electrical Characterization of Surface Passivants for InAs/GaSb Strain Layer Superlattice (SLS) MWIR DetectorsSubhrangshu Mallick
10:40 AM	R7, Late News	3:50 PM	S7, (Student), Simulations of GaP and GaAlAs as the High Band Gap Cell for Multijunction High Efficiency Solar Cell ApplicationsCharles Allen	3:50 PM	T7, (Student), Wet Thermal Oxides of Non-Lattice-Matched InAlP on GaAsJing Zhang
11:00 AM	R8, Selective Growth of Single ZnO NanorodKazunuki Yamamoto	4:10 PM	S8, (Student), Selective Characterization of Deep Levels Defects within Sub-Cells of Dual Junction III-V Solar Cells Grown on Metamorphic SiGe SubstratesMaria Gonzalez	4:10 PM	T8, Improvement in the Insulating Properties of Native Oxides of InAlPPedro Barrios
11:20 AM	R9, (Student), Optical Properties of ZnO NanostructuresTakafumi Yao	4:30 PM	S9, (Student), GaInAs p-Channel HFETs Using Step-Graded AlInAs Metamorphic BuffersMike Morse	4:30 PM	T9, Complete Removal of Fermi Level Pinning at High-k Dielectric/GaAs (001) and (111)B Interfaces by a Silicon Interface Control LayerMasamichi Akazawa
11:40 AM	R10, (Student), Integrated ZnO Nanotips on GaN Light Emitting Diodes for Enhanced Emission EfficiencyJian Zhong	4:50 PM	S10, (Student), Growth, Fabrication, and Characterization of an InGaN/GaN Solar Cell by MBEKristopher Matthews	4:50 PM	T10, Late News

Thursday PM, June 21, 2007					
Session U: Indium Nitride		Session V: Thermoelectric Materials		Session W: Spin-Dependent (or Spintronic) Electronic Materials	
Room: 102		Room: 155		Room: 131	
1:30 PM	U1, (Student), Conduction Band Offset and Schottky Barrier Formation at the InN/GaN HeterojunctionKejia (Albert) Wang	1:30 PM	V1, (Invited), Stable Nanostructured ThermoelectricsMercouri Kanatzidis	1:30 PM	W1, (Student), Correlation between Zeeman Splitting of Band Edges and Curie Temperature in $Ga_{1-x}Mn_xAs$Raja Chakarvorty
1:50 PM	U2, (Student), Effect of MBE Growth Conditions on Multiple Electron Transport in InNTamara Fehlberg			1:50 PM	W2, (Student), Terahertz to Vacuum UV Generalized Magneto-optic Ellipsometry on Chlorine-Doped ZnMnSe: Giant Kerr Effect, Band-to-Band Transitions and Charge Transport ParametersMario Saenger
2:10 PM	U3, Controlling Carrier Type and Concentration in InN through Doping and Substrate ChoiceCraig Swartz	2:10 PM	V2, (Student), Effects of Fermi Level Pinning by Indium on Thermoelectric Properties of $Pb_{(1-x)}Sn_xTe$ AlloysVladimir Jovovic	2:10 PM	W3, (Student), Photoinduced Spin Dynamics in Ferromagnetic GaMnAsJingbo Qi
2:30 PM	U4, Remarkable Reduction of Electron Concentration of In-Rich $In_xGa_{1-x}N$ ($x \sim 0.7$) by Mg DopingAkihiko Kikuchi	2:30 PM	V3, Thermoelectric Properties of Nanostructured Bulk Composites in the $PbTe-Sb_2Te_3$ SystemT. Ikeda	2:30 PM	W4, (Student), Spin Wave Resonances and Surface Spin Pinning in (Ga,Mn)As FilmsYingYuan Zhou
2:50 PM	U5, Optical Hall-Effect in Hexagonal InNTino Hofmann	2:50 PM	V4, Analysis of Thermoelectric Properties of Nanostructured SiGeDaryoosh Vashaee	2:50 PM	W5, Electrically Controlled Non-Volatile Spin-Based Memory DevicesYuriy Semenov
3:10 PM	Break	3:10 PM	Break	3:10 PM	Break
3:30 PM	U6, Direct Write Patterning of InGaN during Molecular Beam Epitaxy and Its Solar Cell ApplicationXiaodong Chen	3:30 PM	V5, (Student), Temperature Dependence of Enhanced Seebeck Coefficient in Ge-Rich Si-Ge AlloysNathaniel Oster	3:30 PM	W6, (Student), Magnetic Anisotropy of Heavily Mn Doped (Ga,Mn)As EpilayersYong Jin Cho
3:50 PM	U7, (Student), Cross-Sectional Cathodoluminescence Study for 1 ML-InN Wells/GaN Matrix MQW Structures Grown by rf-Plasma-Assisted MBEE. S. Hwang	3:50 PM	V6, Thermoelectric Properties Full Heusler Alloys Based on Fe_2VAlDonald Morelli	3:50 PM	W7, (Student), Magnetotransport Properties of GaMnAs Ferromagnetic Semiconductor Tri-Layer Structure Grown on ZnMnSe BufferSanghoon Lee
4:10 PM	U8, (Student), Infrared Cathodoluminescence Measurements of InN FilmsTakanobu Akagi	4:10 PM	V7, (Student), Lanthanum Telluride for High-Temperature TE Applications via Mechanical AlloyingAndrew May	4:10 PM	W8, (Student), Investigation of the Anomalous Hall Effect for (Ga,Mn)As with Different Hole and Mn ConcentrationsZhiguo Ge
4:30 PM	U9, Low Temperature Epitaxial Growth of Nonpolar InN on m-ZnOHiroshi Fujioka	4:30 PM	V8, Zintl Phases as Thermoelectric MaterialsFranck Gascoin	4:30 PM	W9, Novel Ferromagnetic Mn-Doped ZnGeAs ₂ Chalcopyrite with Curie Point Equal to 367 KLiudmila Koroleva
4:50 PM	U10, Late News	4:50 PM	V9, Complex Zintl Phases for Thermoelectric DevicesG. Jeffrey Snyder	4:50 PM	W10, Late News

Thursday PM, June 21, 2007

Session X: Graphene and Carbon Nanotubes Room: 138		Session Y: ZnO: Characterization and Devices Room: 141		NOTES
1:30 PM	X1, Strong Field Effect in Epitaxial Graphene on a SiC SubstrateGong Gu	1:30 PM	Y1, (Student), Influence of Surface Polarity on the Electrical and Optical Properties of Bulk ZnOMartin Allen	
1:50 PM	X2, (Student), Morphology and Electronic States of Graphene on SiC (0001) SurfacesShu Nie	1:50 PM	Y2, Using the Exciton Band Edge to Assess ZnO Material Quality and the Effects of Internal and Externally Applied Electric FieldsJohn Muth	
2:10 PM	X3, Fabrication and Characterization of Graphene Transistor Grown on 6H-SiCKanji Yoh	2:10 PM	Y3, (Student), Polarization Coupled Response of ZnO-BaTiO ₃ Heterojunctions: A Model ApproachVenkata Voora	
2:30 PM	X4, (Invited), Charge and Spin Coherent Transport Studies in GrapheneBarbaros Oezylimaz	2:30 PM	Y4, (Student), Annealing Studies on Zinc Oxide Thin Films Deposited by Magnetron SputteringTingfang Yen	
		2:50 PM	Y5, Effects of Electron-Irradiation and Annealing on Deep Centers in Hydrothermal ZnOZhaoqiang Fang	
3:10 PM	Break	3:10 PM	Break	
3:30 PM	X5, (Student), Determination Method of Energy Band Gap of Carbon Nanotube by High Temperature Dependence of CurrentMasatoshi Maeda	3:30 PM	Y6, (Student), Low Temperature PECVD ZnO Thin Film Transistors and CircuitsJie Sun	
3:50 PM	X6, (Student), Silicon Supported Porous Anodic Alumina Templates with Long-Range Order for Vertical Nanoscale DevicesJoshua Smith	3:50 PM	Y7, (Student), Fabrication and Performance of Zinc Oxide Thin Film TransistorsYongwoo Jeong	
4:10 PM	X7, (Student), Room Temperature CNT Single Electron Transistor Formed by Plasma Induced Defect ProcessShin Iwasaki	4:10 PM	Y8, (Student), Interface Study of ZnO Nanowire Transistors Using Low-Frequency Noise and Temperature-Dependent I-V MeasurementsSanghyun Ju	
4:30 PM	X8, Growth of Single and Double-Walled Carbon Nanotubes on a Substrate Using Catalyst Nanoparticles Size-Classified with an ImpactorDaiyu Kondo	4:30 PM	Y9, (Student), Photodetection and Electroluminescence from Optoelectronic Devices Based on Sb-Doped p-ZnOLeelaprasanna Mandalapu	
4:50 PM	X9, Late News	4:50 PM	Y10, CdZnO/MgZnO Multilayered Structures for Photonic Application: Growth and DevicesAndrei Osinsky	

Friday AM, June 22, 2007					
Session Z: Molecular Electronics: Devices, Materials and Contacts Room: 126		Session AA: Oxide Thin Film Integration II Room: 129		Session BB: III-Nitride Processing and Characterization Room: 102	
8:20 AM	Z1, (Student), Ultra-High Vacuum Scanning Tunneling Microscopy Characterization of Nitroxyl Free Radicals on the Si(111)-7x7 SurfaceQing Hua Wang	8:20 AM	AA1, (Student), Physical and Electrical Characterization of Nb-W, Ti-W and Pt-Ti Bilayer and Alloy Metal Gate Electrodes for Advanced CMOS ApplicationsGloria Wong	8:20 AM	BB1, Novel Concepts for AlGa _N /MgZnO Hetero-Interfaces and DevicesAndrei Osinsky
8:40 AM	Z2, (Student), Molecular Orbital and Dipole Effects in Metal-Molecule-Silicon SystemsAdina Scott	8:40 AM	AA2, (Student), Two-Step Annealing Sili-cidation Process in NiSi-Gated MOSFETJun Liu	8:40 AM	BB2, Inhomogeneous Nucleation of III-Nitride Films on 4H-SiC Mesa SubstratesYousuf Picard
9:00 AM	Z3, (Student), Atomic Resolution Assembly and Characterization of Organohalide Functionalized Silicon SurfacesMichael Walsh	9:00 AM	AA3, (Student), Electrical Characterization of Molecular Beam Deposited LaAlO ₃ -GaAs and Annealing EffectsDonghun Choi	9:00 AM	BB3, GaN Doped with Neodymium by Plasma-Assisted Molecular Beam EpitaxyEric Readinger
9:20 AM	Z4, Electronic Properties of Redox-Active Organic Molecules in Metal-Molecule-Metal JunctionsAjit Mahapatro	9:20 AM	AA4, MBE Growth of Ga ₂ O ₃ and (InGa) ₂ O ₃ Films with Ultraviolet Optical FunctionsShizuo Fujita	9:20 AM	BB4, Deep Level Transient Spectroscopy of AlGa _N /Ga _N Heterostructure Treated by Fluoride-Based PlasmaLiwu Lu
9:40 AM	Z5, (Student), Dramatic Resistance Increase and Magnetic Ordering with Molecular Spin-Valve ElectrodesPawan Tyagi	9:40 AM	AA5, (Student), Molecular Beam Epitaxy of YMnO ₃ on c-Plane GaNCameron Keenan	9:40 AM	BB5, (Student), Characterization of Mg-Doped AlInN Annealed in Nitrogen and Oxygen AmbientsAn-Ting Cheng
10:00 AM	Z6, (Student), Measurement of Tunneling Currents through Alkanes Assembled on Silicon with Aluminum ContactsDivesh Kapoor	10:00 AM	Break	10:00 AM	Break
10:20 AM		10:20 AM	AA6, Structure and Ion Conduction Phenomena in Oxide Thin Films and NanostructuresShriram Ramanathan	10:20 AM	BB6, (Student), A Study of MgO and AlN Caps for Protecting the GaN Surface during Ultra-Fast Microwave AnnealingSiddarth Sundaresan
10:40 AM		10:40 AM	AA7, (Student), Growth of Either (001) or (111) Epitaxial CeO ₂ on R-Cut Sapphire by Modifying Conditions and an Analysis of the In-Plane Domain Matching Epitaxy Operative for Both OrientationsMadhana Sunder	10:40 AM	BB7, (Student), Comparative Study of As-Grown AlGaAs/GaAs/GaAs HBTs and Wafer Fused AlGaAs/GaAs/GaN HBTsChuanxin Lian
11:00 AM		11:00 AM	AA8, (Student), High-Resolution Synchrotron X-Ray Studies of Multiferroic BiFeO ₃ Thin FilmsJeffrey Klug	11:00 AM	BB8, Chemical Mechanical Polishing of GaNSumiko Hayashi
11:20 AM		11:20 AM	AA9, Epitaxial Growth of Rock Salt Oxides on Perovskite SubstratesVolker Heydemann	11:20 AM	BB9, Cleaved Nitride Semiconductor Laser MirrorsWei-Li Chen
11:40 AM		11:40 AM	AA10, RF Plasma MBE Growth and Characterization of BiFeO ₃ and Bi ₂ FeCrO ₆ Multiferroic Thin FilmsSiddhartha Ghosh	11:40 AM	BB10, Late News

Friday AM, June 22, 2007

Session CC: Compound Semiconductor Nanowires Room: 155		Session DD: Narrow Gap Materials and Devices Room: 131		Session EE: Epitaxy for Devices Room: 138	
8:20 AM	CC1, III-V Nanowire Growth Mechanism: VLS or VSSShadi A. Dayeh	8:20 AM	DD1, Long-Wavelength Light Emitters on Lattice-Engineered GaAs SubstratesKenneth Lee	8:20 AM	EE1, (Student), MBE Grown Multifunctional Heterostructures-Combining Ferromagnets with Insulators and FerroelectricsSwadesh Srivastava
8:40 AM	CC2, (Student), V/III Ratio Effects on the Shape and Optical Properties of InP Nanowires Grown on SiliconMichael Moewe	8:40 AM	DD2, Electric Field and Size Dependence of Magnetic Field Sensitivity in an InAs 2-DEGThomas Boone	8:40 AM	EE2, (Student), MOCVD Growth of InAlGaAs-InP Light-Emitting Transistors Operating at ~1.55 mmY. Huang
9:00 AM	CC3, (Student), Photocurrent Polarization Anisotropy of Randomly Oriented Nanowires NetworkYanghai Yu	9:00 AM	DD3, Comparison of MBE Growth of InSb on Si (001) and GaAs (001)W. Masselink	9:00 AM	EE3, The Development of InGaAs Thermophotovoltaic Cells on InP Using Strain-Relaxed InPAs BuffersJ. G. Cederberg
9:20 AM	CC4, Growth and Characterization of Vertically Aligned III-Nitride Nanowires and Heterostructure NanowiresQiming Li	9:20 AM	DD4, (Student), Capacitance-Voltage Characterization of InSb MOS Structures with ALD High-k Gate DielectricsTian Yang	9:20 AM	EE4, Enhanced Mobility Delta-Doped p-Channel AlInAs/GalnAs HFETs on InPChanghyun Yi
9:40 AM	CC5, Mechanical Properties of C-Axis Oriented Gallium Nitride NanowiresShawn Tanner	9:40 AM	DD5, (Student), Thermally Stable Gate Metallizations for Antimonide-Based High Electron Mobility Transistors with Indium Arsenide ChannelsTrevor Buehl	9:40 AM	EE5, (Student), Stress in Nano-Scale Patterned Strained Silicon/Strained Germanium/Strained Silicon Heterostructures on InsulatorPouya Hashemi
10:00 AM	Break	10:00 AM	Break	10:00 AM	Break
10:20 AM	CC6, Correlation of Luminescence, Electrical Transport, and Growth Temperature for Individual GaN NanowiresAlec Talin	10:20 AM	DD6, Heavily Strained InGaAsSb/AlGaAsSb Quantum Well Heterostructures for Optoelectronic ApplicationsDmitri Donetsky	10:20 AM	
10:40 AM	CC7, Time-Resolved and CW Photoluminescence Measurements on Strained and Unstrained GaN Nanowires Grown by Catalyst-Free MBEJohn Schlager	10:40 AM	DD7, (Student), Arsenic-Free Long Wavelength Mid-IR Emitters on GaAs SubstrateYaxin Yu	10:40 AM	
11:00 AM	CC8, Persistent Photoconductivity Studies of GaN Nanowires and Nanowire Bridge StructuresNorman Sanford	11:00 AM	DD8, Extended Wavelength Lattice-Mismatched InP-Based Avalanche PhotodiodesChristine Wang	11:00 AM	
11:20 AM	CC9, (Student), Effects of Surface Fixed Charges and Interface Trap Charges on Transport Properties of InAs Nanowire TransistorsQingling Hang	11:20 AM	DD9, 1.65 mm III-Sb Quantum Well Lasers on GaAs Substrates Enabled by Interfacial Misfit Dislocation (IMF) Based NucleationGanesh Balakrishnan	11:20 AM	
11:40 AM	CC10, (Student), Enhancement of Carrier Mobility in Semiconductor Nanostructures Using Dielectric Mismatch EffectAniruddha Konar	11:40 AM	DD10, Fabrication and Characterization of a Photonic Crystal DFB Interband Cascade Laser Operating at 3.3 mmJill Nolde	11:40 AM	

Friday AM, June 21, 2007				
Session FF: III-Nitride: Pseudo-Substrates Room: 138		Session GG: Dilute Nitride Semiconductors Room: 141		NOTES
8:20 AM		8:20 AM	GG1, Optical Properties and Characteristics of Dilute Nitride InN(As)Sb Quantum Well and Quantum Dot Grown by MBE for Infrared Sensors ApplicationSeongsin Kim	
8:40 AM		8:40 AM	GG2, (Student), Composition Fluctuation and Carrier Localization in GaAs(In,Sb)N Quantum WellsKai Sun	
9:00 AM		9:00 AM	GG3, Effects of Different Plasma Species on the Optical Properties of Dilute Nitrides Grown by Plasma-Assisted Molecular-Beam EpitaxyMichael Oye	
9:20 AM		9:20 AM	GG4, Characteristics of GaAsSbN/InP and GaSbN/GaSb Grown by Metalorganic Chemical Vapor DepositionDapeng Xu	
9:40 AM		9:40 AM	GG5, (Student), High Sb-Content GaAsSb-GaAsN Type-II Quantum Well 'W' Structures for Long Wavelength Emission on GaAs SubstratesManish Rathi	
10:00 AM		10:00 AM	Break	
10:20 AM	FF1, Fabrication of 3-Inch Freestanding GaN Substrates by Hydride Vapor Phase Epitaxy with Void-Assisted SeparationYuichi Oshima	10:20 AM		
10:40 AM	FF2, Mechanisms of AlGaIn Growth with Reduced Dislocation Density on Patterned GaNDavid Follstaedt	10:40 AM		
11:00 AM	FF3, (Student), Microstructural Evolution in the Initial Growth Stage of m-Plane GaN on m-Plane SiC with a High-Temperature Grown AlN BufferQian Sun	11:00 AM		
11:20 AM	FF4, (Student), Growth and Characterizations of Auto-Roughened LED Grown on Wet-Etched Stripe-Patterned Sapphire SubstrateKar Wei Ng	11:20 AM		
11:40 AM	FF5, Low Leakage Current Schottky Diodes Fabricated from Low Defect Density MOCVD GaN Grown by Pendeo - EpitaxyMichael Derenge	11:40 AM		